ABSTRACT OF THE DISCLOSURE

The semiconductor device fabrication method comprises the step of forming electrodes 20 in a first element region 14n and in a second element region 14p; the step of forming a first resist film 22 which is opened in the first element region 14n; the step of forming a first dopant diffused region 28 with the first resist film 22 and the gate electrode 20 as a mask; the first ashing processing step of ashing the first resist film 22; the step of forming a sidewall insulation film 42 over the side wall of the gate electrode 20; the step of forming a second resist film 44 which is opened in the first element region 14n; the forming a second dopant diffused region 48 with the second resist film 44, the gate electrode 20 and the sidewall insulation film 42 as a mask; and the second ashing processing step for ashing the second resist film 44. The ashing processing period of time in the first ashing processing step is shorter than the ashing processing period of time in the second ashing processing step.